

SANYO SEMICONDUCTOR

2SD995

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NPN Triple Diffused Mesa Type Silicon Transistor
For H-Deflection Output with High Voltage (With Damper Diode)

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V _{CB0}	2500	V
Collector to Emitter Voltage	V _{CE0}	900	V
Emitter to Base Voltage	V _{EB0}	6	V
Collector Current	I _C	3	A
Collector Current (peak)	i _{cp}	7	A
Collector Dissipation	P _C	3	W
	P _C	50	W
	T _c	25	°C
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-40~+150	°C

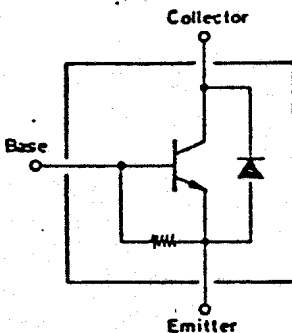
Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cut off Current	I _{CES}			1.0	mA
Emitter Cut off Current	I _{EBO}		40	130	mA
Emitter to Base Voltage	V _{EB0}	6.0			V
Emitter to Collector Voltage	V _{EC0}			2.0	V
DC Current Gain	h _{FE}		3*	15*	
C-E Saturation Voltage	V _{CE(sat)}			5	V
B-E Saturation Voltage	V _{BE(sat)}			1.3	V
C-E Sustain Voltage	V _{CE(sus)}	900			V
Fall Time	t _f			1.0	μs

* 2SD995 are classified according to 1.5A h_{FE} as follows.

3 K 9 5 M 15

Equivalent Circuit



Case Outline (UNIT:mm)

